UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 6,916,699 B1

: July 12, 2005

DATED

INVENTOR(S): Vishnu K. Agarwal

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [56], References Cited, U.S. PATENT DOCUMENTS,

"5,552,341 A

9/1996

Lee

438/668" should read

-- 5,552,341 A

9/1996 Lee 437/192 --.

Column 1,

Line 53, "tungsten nitride WNx1, wherein X is a number greater than" should read -- tungsten nitride WN_x, wherein X is a number greater than --.

Column 2,

Line 4, "cause the oxygen at the tungsten nitride surface to diff-use" should read -- cause the oxygen at the tungsten nitride surface to diffuse --.

Line 10, "coupled in series, wherein the HSG/Ta₂O₅WN_x layers serve" should read -- coupled in series, wherein the HSG/Ta₂O₅/WNx layers serve --.

Line 14, "Ta₂O₅WNx/polysilicon capacitor that was intended to be" should read -- Ta₂O₅/WNx/polysilicon capacitor that was intended to be --.

Line 18, "as the bottom plate of a capacitor, underlying the Ta₂O₅," should read -- as the bottom plate of a capacitor, underlying the Ta₂O₅ --.

Column 4,

Line 40, "nitride layer 28 exposed in situ to a N2 and H2 plasma The" should read -- nitride layer 28 exposed in situ to a N₂ and H₂ plasma. The --.

Line 52, "(RF) power ranging from about 50 to about 1000 W; a" should read -- (RF) power ranging from about 50 to about 1000W; a --.

Column 5,

Line 42, "ranging from about 50 to about 1000 W; a pressure ranging" should read -- ranging from about 50 to about 1000W; a pressure ranging --.

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 6,

Line 21, "used to provide the. tungsten nitride layer 28 and one of the" should read -- used to provide the tungsten nitride layer 28 and one of the --.

Signed and Sealed this

Twenty-first Day of March, 2006

JON W. DUDAS
Director of the United States Patent and Trademark Office